

EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 10188780
PUBLICATION DATE : 21-07-98

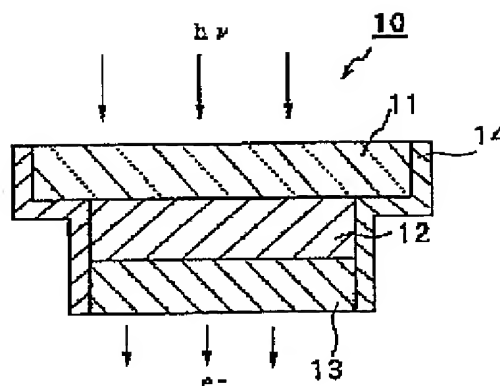
APPLICATION DATE : 24-12-96
APPLICATION NUMBER : 08343884

APPLICANT : HAMAMATSU PHOTONICS KK;

INVENTOR : TAKEUCHI JUNICHI;

INT.CL. : H01J 1/34

TITLE : PHOTOELECTRIC SURFACE



ABSTRACT : PROBLEM TO BE SOLVED: To provide a photoelectric surface having a semiconductor or the like that is excellent in crystallinity.

SOLUTION: This photoelectric surface 10 includes a substrate 11 made from LiAlO_2 (LAO), a substrate protection layer 12 formed on the substrate 11 to thermally protect the substrate 11, and an active layer 13 formed on the substrate protection layer 12 to generate photoelectrons through the incidence of light, the substrate protection layer 12 and the active layer 123 being made from a crystal composed of at least one kind of component selected from a group consisting of AlN, GaN, and InN and being sensitive to ultraviolet light. This constitution allows the crystal and LAO to have almost equal lattice constants, improving lattice mismatching. Therefore, introduction of crystal defects depending on the sensitivity of the photoelectric surface 10 is restrained, and the substrate protection layer 12 and the active layer 13 are given an excellent crystallinity.

COPYRIGHT: (C)1998,JPO